

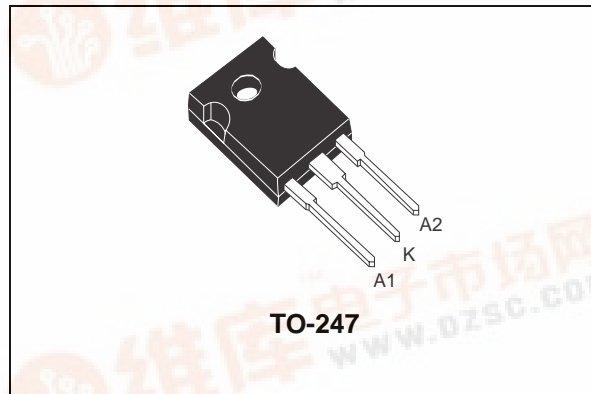


STTH3003CW

HIGH FREQUENCY SECONDARY RECTIFIER

MAJOR PRODUCT CHARACTERISTICS

I_{F(AV)}	2 x 15 A
V_{RRM}	300 V
T_{j (max)}	175 °C
V_{F (max)}	1 V
trr (max)	40 ns



FEATURES AND BENEFITS

- COMBINES HIGHEST RECOVERY AND REVERSE VOLTAGE PERFORMANCE
- ULTRA-FAST, SOFT AND NOISE-FREE RECOVERY

DESCRIPTION

Dual center tap Fast Recovery Epitaxial Diodes suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-247 this device is intended for secondary rectification.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		300	V
I _{F(RMS)}	RMS forward current		30	A
I _{F(AV)}	Average forward current	T _c = 135°C δ = 0.5	Per diode 15 Per device 30	A
I _{FSM}	Surge non repetitive forward current	tp = 10 ms sinusoidal	140	A
I _{RSM}	Non repetitive peak reverse current	tp = 20 μs square	7	A
T _{stg}	Storage temperature range		-65 +175	°C
T _j	Maximum operating junction temperature		+175	°C



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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	Per diode	2.0	°C/W
		Total	1.05	
R _{th(c)}		Coupling	0.1	

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	V _R = 300 V	T _j = 25°C			40	μA
			T _j = 125°C		40	400	
V _F **	Forward voltage drop	I _F = 15 A	T _j = 25°C			1.25	V
			T _j = 125°C		0.85	1	

Pulse test : * t_p = 5 ms, δ < 2 %

** t_p = 380 μs, δ < 2%

To evaluate the maximum conduction losses use the following equation :

$$P = 0.75 \times I_{F(AV)} + 0.017 I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Tests conditions		Min.	Typ.	Max.	Unit
t _{rr}	I _F = 0.5 A I _{rr} = 0.25 A I _R = 1A	T _j = 25°C			30	ns
	I _F = 1 A dI _F /dt = - 50 A/μs V _R = 30V				40	
t _{fr}	I _F = 15 A dI _F /dt = 100 A/μs	T _j = 25°C			300	ns
V _{FP}	V _{FR} = 1.1 x V _F max.				3.5	
S _{factor}	V _{CC} = 200 V I _F = 15 A	T _j = 125°C		0.3		-
I _{RM}	dI _F /dt = 200A/μs				8.5	A

Fig. 1: Conduction losses versus average current (per diode).

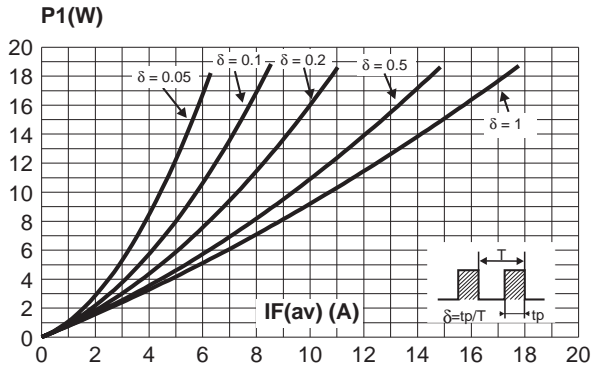


Fig. 2: Forward voltage drop versus forward current (maximum values, per diode).

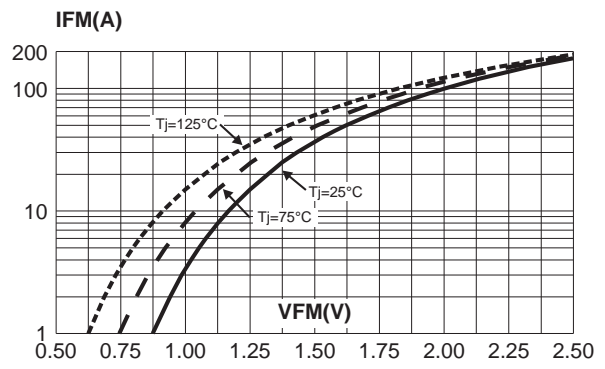


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

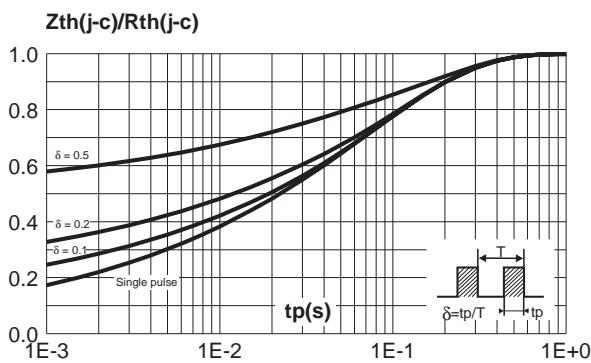


Fig. 4: Peak reverse recovery current versus dIF/dt (90% confidence, per diode).

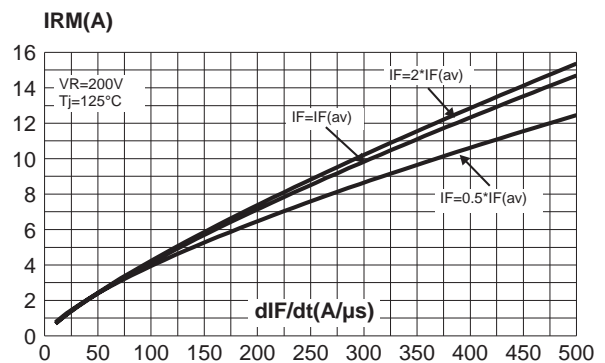


Fig. 5: Reverse recovery time versus dIF/dt (90% confidence, per diode).

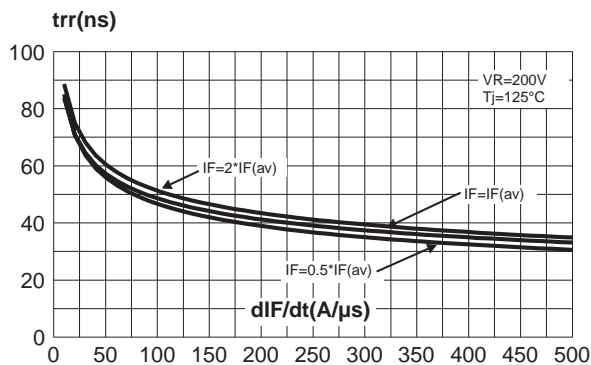
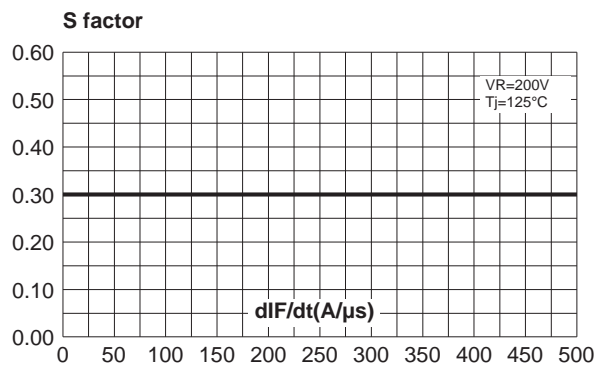


Fig. 6: Softness factor versus dIF/dt (typical values, per diode).



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Fig. 7: Relative variation of dynamic parameters versus junction temperature (reference: $T_j = 125^\circ\text{C}$).

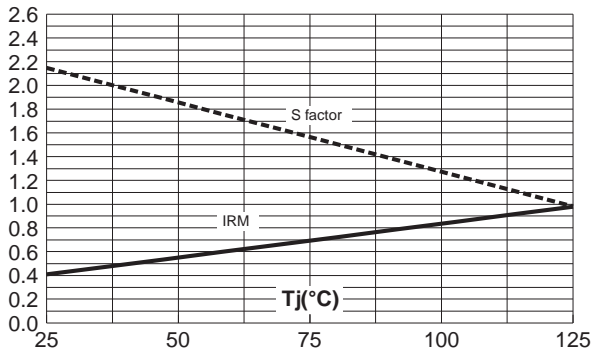


Fig. 8: Transient peak forward voltage versus dI_F/dt (90% confidence, per diode).

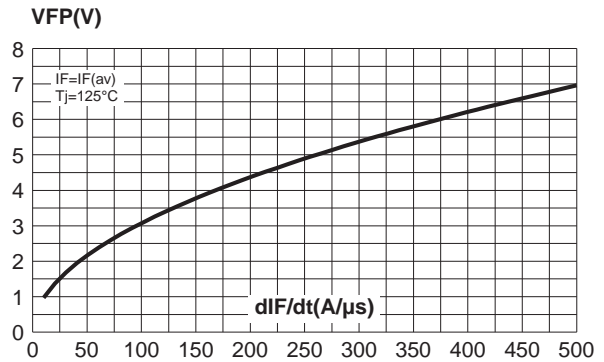
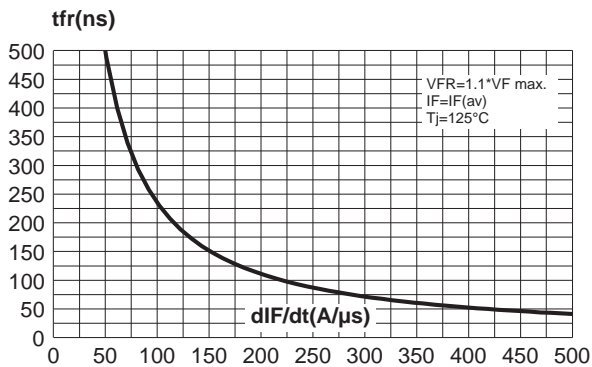
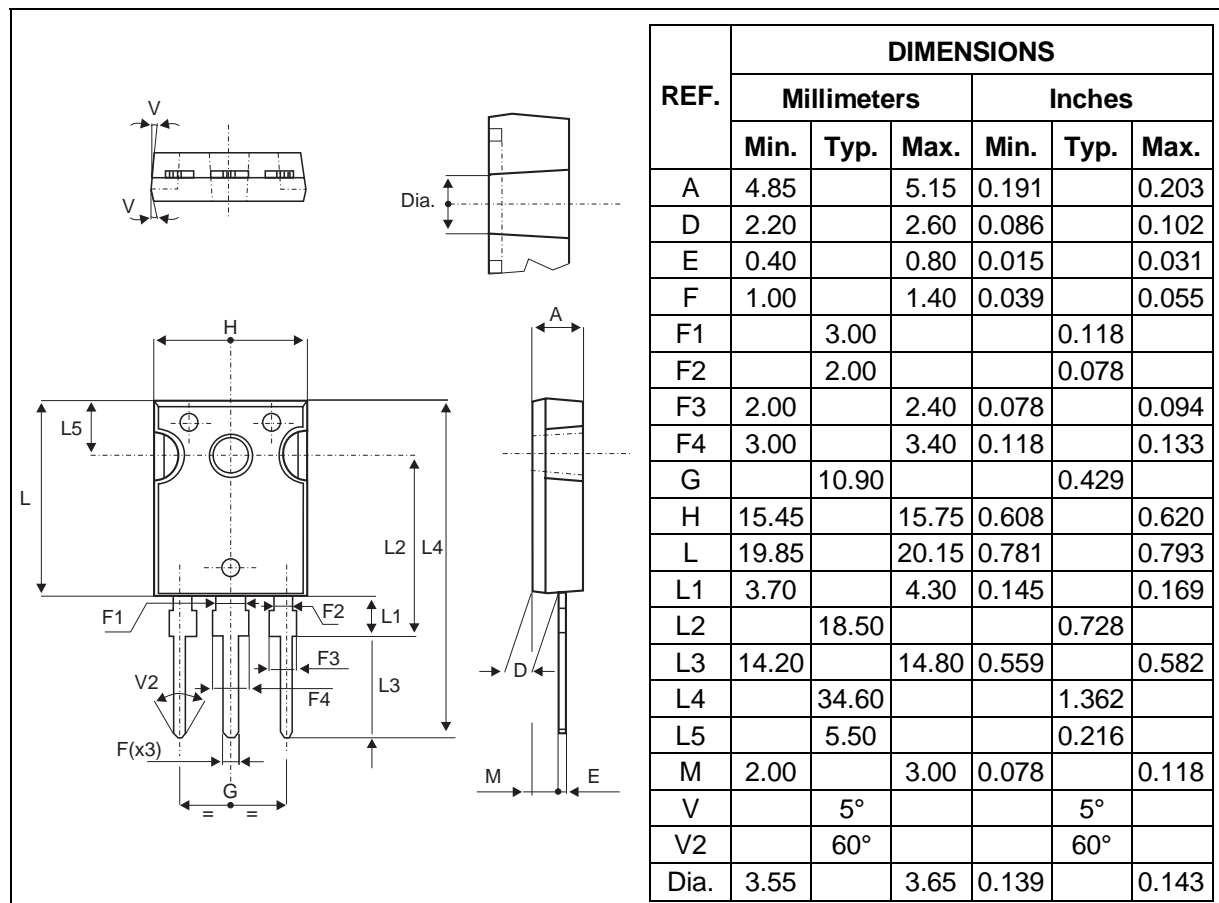


Fig. 9: Forward recovery time versus dI_F/dt (90% confidence, per diode).



PACKAGE MECHANICAL DATA
 TO-247


Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH3003CW	STTH3003CW	TO-247	4.36g	30	Tube

- Cooling method: by conduction (C)
- Recommended torque value: 0.8 N.m.
- Maximum torque value: 1.0 N.m.
- Epoxy meets UL 94,V0

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